

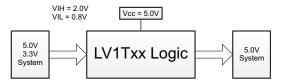
**SN74LV1T34** 

JAJSOT4E - DECEMBER 2013 - REVISED FEBRUARY 2024

# SN74LV1T34 単一電源シングル・バッファ・ゲート CMOS ロジック・レベル・ シフタ

## 1 特長

- JESD 17 準拠で 250mA 超のラッチアップ性能
- 5V、3.3V、2.5V、1.8V V<sub>CC</sub> の単一電源電圧トランスレ
- 動作範囲:1.65V~5.5V
- 昇圧変換:
  - 1.8V V<sub>CC</sub> で 1.2V<sup>(1)</sup> から 1.8V
  - 2.5V V<sub>CC</sub> で 1.5V<sup>(1)</sup> から 2.5V
  - 3.3V V<sub>CC</sub> で 1.8V<sup>(1)</sup> から 3.3V
  - 5.0V V<sub>CC</sub> で 3.3V から 5.0V
- 降圧変換:
  - 1.8V V<sub>CC</sub> で 3.3V から 1.8V
  - 2.5V V<sub>CC</sub> で 3.3V から 2.5V
  - 3.3V V<sub>CC</sub> で 5.0V から 3.3V
- ロジック出力は V<sub>CC</sub> を基準とする
- 出力駆動能力:
  - 5V で 8mA の出力駆動能力
  - 3.3V で 7mA の出力駆動能力
  - 1.8V で 3mA の出力駆動能力
- 3.3V の V<sub>CC</sub> で最大 50MHz の動作を特性評価
- 入力ピンの許容電圧:5V
- -40°C~125°Cの動作温度範囲



- 標準ロジックピン配置をサポート
- CMOS 出力 B は AUP1G および LVC1G ファミリと互 換性あり。1

# 2 アプリケーション

- テレコム
- 携帯用アプリケーション
- サーバー
- PC とノート PC

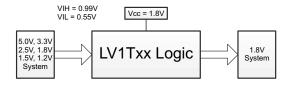
## 3 概要

SN74LV1T34 は、電圧レベル変換アプリケーションをサ ポートするために入力スレッショルドを低減した、シングル バッファゲートです。

#### パッケージ情報

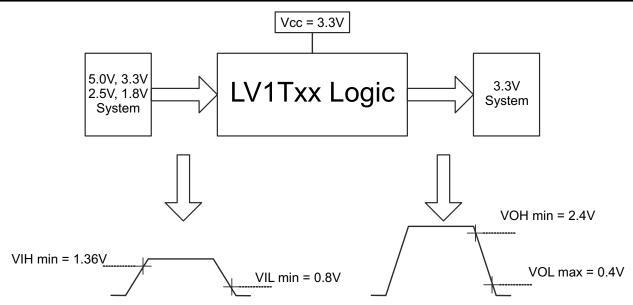
	部品番号	パッケージ <sup>(1)</sup>	パッケージ <sup>(2)</sup>	本体サイズ(3)
5	SN74LV1T34	DBV (SOT-23, 5)	2.90mm × 2.8mm	2.90mm × 1.60mm
	3N/4LV1134	DCK (SC70, 5)	2.00mm × 2.1mm	2.00mm × 1.25mm

- 詳細については、セクション 12 を参照してください。
- パッケージ サイズ (長さ×幅) は公称値であり、該当する場合はピ ンも含まれます。
- 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。



より低い V<sub>CC</sub> の条件については、V<sub>IH</sub>/V<sub>IL</sub> と出力駆動能力を参照。





1.8V から 3.3V にレベル変換する場合のスイッチング スレッショルド

English Data Sheet: SCLS743



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Product Folder Links: SN74LV1T34 English Data Sheet: SCLS743



# **4 Related Products**

DEVICE	PACKAGE	DESCRIPTION
SN74LV1T00	DCK, DBV	2-Input Positive-NAND Gate
SN74LV1T02	DCK, DBV	2-Input Positive-NOR Gate
SN74LV1T04	DCK, DBV	Inverter Gate
SN74LV1T08	DCK, DBV	2-Input Positive-AND Gate
SN74LV1T17	DCK, DBV	Single Schmitt-Trigger Buffer Gate
SN74LV1T14	DCK, DBV	Single Schmitt-Trigger Inverter Gate
SN74LV1T32	DCK, DBV	2-Input Positive-OR Gate
SN74LV1T34	DCK, DBV	Single Buffer Gate
SN74LV1T86	DCK, DBV	Single 2-Input Exclusive-Or Gate
SN74LV1T125	DCK, DBV	Single Buffer Gate with 3-state Output
SN74LV1T126	DCK, DBV	Single Buffer Gate with 3-state Output
SN74LV4T125	RGY, PW	Quadruple Bus Buffer Gate With 3-State Outputs

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# **5 Pin Configuration and Functions**

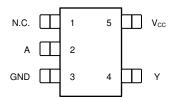


図 5-1. DCK or DBV Package, 5-Pin SC70 or SOT-23 (Top View)

表 5-1. Pin Functions

PIN		TYPE <sup>(1)</sup>	DESCRIPTION		
NAME	NO.	ITPE\"	DESCRIPTION		
NC	1	_	Not internally connected		
Α	2	I	Input A		
GND	3	G	Ground		
Y	4	0	Output Y		
V <sub>CC</sub>	5	Р	Positive supply		

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

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Product Folder Links: SN74LV1T34



# **6 Specifications**

# **6.1 Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage range		-0.5	7.0	V
VI	Input voltage range <sup>(2)</sup>		-0.5	7.0	V
Vo	Voltage range applied to any	output in the high or low state <sup>(2)</sup>	-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>1</sub> < 0		-20	mA
I <sub>OK</sub>	Output clamp current	$V_O < 0$ or $V_O > V_{CC}$		±20	mA
Io	Continuous output current			±25	mA
	Continuous current through V	CC or GND		±50	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	
V <sub>(ESD)</sub>	Electrostatic discharge Machine Model (MM), per JEDEC specification	Machine Model (MM), per JEDEC specification	±200	V
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	±1000	

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		1.6	5.5	V
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 1.8 V		-3	
lı.	High level output current	V <sub>CC</sub> = 2.5 V		-5	mA
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 3.3 V		-7	ША
		V <sub>CC</sub> = 5.0 V		-8	
		V <sub>CC</sub> = 1.8 V		3	
	Low-level output current	V <sub>CC</sub> = 2.5 V		5	m Λ
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 3.3 V		7	mA
		V <sub>CC</sub> = 5.0 V		8	
		V <sub>CC</sub> = 1.8 V		20	
Δt/Δν	Input transition rise or fall rate	V <sub>CC</sub> = 3.3 V or 2.5 V		20	ns/V
	V <sub>CC</sub> = 5.0 V			20	
T <sub>A</sub>	Operating free-air temperature		-40	125	°C

<sup>(1)</sup> All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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<sup>(2)</sup> The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



## **6.4 Thermal Information**

	THERMAL METRIC(1)	DBV	DCK	UNIT
	THERMAL METRIC	5 PINS	5 PINS	ONIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	278	289.2	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

#### 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

D/	DAMETED	TEST CONDITIONS	V <sub>cc</sub>	T <sub>A</sub> =	25°C		$T_A = -40^\circ$	C to +125°	С	UNIT
PARAMETER		TEST CONDITIONS	Vcc	MIN	TYP	MAX	MIN	TYP	MAX	UNI
			V <sub>CC</sub> = 1.65 V to 1.8 V	0.95			1			
			V <sub>CC</sub> = 2.0 V	0.99			1.03			
			V <sub>CC</sub> = 2.25 V to 2.5 V	1.145			1.18			
,	High-level		V <sub>CC</sub> = 2.75 V	1.22			1.25			V
√ <sub>IH</sub>	input voltage		V <sub>CC</sub> = 3 V to 3.3 V	1.37			1.39			V
			V <sub>CC</sub> = 3.6 V	1.47			1.48			
			V <sub>CC</sub> = 4.5 V to 5.0 V	2.02			2.03			
			V <sub>CC</sub> = 5.5 V	2.1			2.11			
			V <sub>CC</sub> = 1.65 V to 2.0 V			0.57			0.55	
,	Low-level		V <sub>CC</sub> = 2.25 V to 2.75 V			0.75			0.71	.,
V <sub>IL</sub>	input voltage		V <sub>CC</sub> = 3 V to 3.6 V			0.8			0.65	V
			V <sub>CC</sub> = 4.5 V to 5.5 V			0.8			0.8	
		I <sub>OH</sub> = -20 μA	1.65 V to 5.5 V	V <sub>CC</sub> - 0.1			V <sub>CC</sub> - 0.1			
			1.65 V	1.28			1.21			
	High-level output	I <sub>OH</sub> = –2.0 mA	1.8 V	1.5			1.45			
		I <sub>OH</sub> = -3.0 mA	2.3 V	2			1.93			
		I <sub>OH</sub> = -3.0 mA	2.5 V	2.25			2.15			
V <sub>OH</sub>		I <sub>OH</sub> = -3.0 mA	0.01/	2.78			2.7			V
	voltage	I <sub>OH</sub> = -5.5 mA	3.0 V	2.6			2.49			
		I <sub>OH</sub> = -5.5 mA	3.3 V	2.9			2.8			
		I <sub>OH</sub> = -4.0 mA	4.5.4	4.2			4.1			
		I <sub>OH</sub> = -8.0 mA	4.5 V	4.1			3.95			
		I <sub>OH</sub> = -8.0 mA	5.0 V	4.6			4.5			
		I <sub>OL</sub> = 20 μA	1.65 V to 5.5 V			0.1			0.1	
		I <sub>OL</sub> = 2.0 mA	1.65 V			0.2			0.25	
	Low-level	I <sub>OL</sub> = 3.0 mA	2.3 V			0.15			0.2	
/ <sub>OL</sub>	output	I <sub>OL</sub> = 3.0 mA	0.01/			0.11			0.15	V
	voltage	I <sub>OL</sub> = 5.5 mA	3.0 V			0.21			0.252	
		I <sub>OL</sub> = 4.0 mA	4.5.4			0.15			0.2	
		I <sub>OL</sub> = 8.0 mA	4.5 V			0.3			0.35	
I	Input leakage current	A input; V <sub>I</sub> = 0 V or V <sub>CC</sub>	0 V, 1.8 V, 2.5 V, 3.3 V, 5.5 V			0.1			±1	μΑ
			5.0 V			1			10	
	Static supply	$V_I = 0 \text{ V or } V_{CC}$	3.3 V			1			10	
CC	current	I <sub>O</sub> = 0; open on loading	2.5 V			1			10	μΑ
			1.8 V			1			10	

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over recommended operating free-air temperature range (unless otherwise noted)

DΛ	RAMETER	TEST CONDITIONS	V <sub>cc</sub>	T <sub>A</sub> = 25°C	T <sub>A</sub> = -40°C to +125°C	UNIT
FA	NAMETER	TEST CONDITIONS	VCC	MIN TYP MAX	MIN TYP MAX	
ΔI <sub>CC</sub>	Additional static supply	One input at 0.3 V or 3.4 V, Other inputs at 0 or V <sub>CC</sub> , I <sub>O</sub> = 0	5.5 V	1.35	1.5	mA
	static supply current	One input at 0.3 V or 1.1 V Other inputs at 0 or V <sub>CC</sub> , I <sub>O</sub> = 0	1.8 V	10	10	μА
C <sub>i</sub>	Input capacitance	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V	2 10	2 10	pF
Co	Output capacitance	V <sub>O</sub> = V <sub>CC</sub> or GND	3.3 V	2.5	2.5	pF

# **6.6 Switching Characteristics**

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM	то	FREQUENCY	V	CL	TA	= 25°	С	T <sub>A</sub> = -6	5°C to 1	25°C	UNIT					
PARAMETER	(INPUT)	(OUTPUT)	(TYP) V <sub>CC</sub>	V CC	6	MIN	TYP	MAX	MIN	TYP	MAX	ONII					
				5.0 V	15 pF		2.7	5.5		3.4	6.5	ns					
			DC to 50 MHz	3.0 V	30 pF		3	6.5		4.1	7.5	113					
					3.3 V	DO 10 30 WI 12	DO 10 30 WI 12	DO 10 30 WH 12		15 pF		4	7		5	8	ns
•	Any In	Y				3.3 V	30 pF		4.9	8		6	9	115			
t <sub>pd</sub>	Ally III	Ally III	DC to 25 MHz	DC to 25 MHz	2.5 V	15 pF		5.8	8.5		6.8	9.5	ns				
				2.5 V	30 pF		6.5	9.5		7.5	10.5	115					
			DC to 15 M	DC to 15 MHz 1.8 V	DC to 15 MHz 1.8 V	DC to 15 MHz 1.8 V	DC to 15 MHz 1 9 V	181/	15 pF		10.5	13		11.8	14	ns	
			DC to 15 MHz				1.0 V	30 pF		12	14.5		12	15.5	115		

# **6.7 Operating Characteristics**

 $T_A = 25^{\circ}C$ 

	PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	TYP	UNIT	
			1.8 V ± 0.15 V	14		
C <sub>pd</sub>	Power dissipation capacitance	f = 1 MHz and 10 MHz	2.5 V ± 0.2 V	14	pF	
	Power dissipation capacitance	I – I MINZ AND IO MINZ	3.3 V ± 0.3 V	14	pr	
			5.5 V ± 0.5 V	14		

Product Folder Links: SN74LV1T34

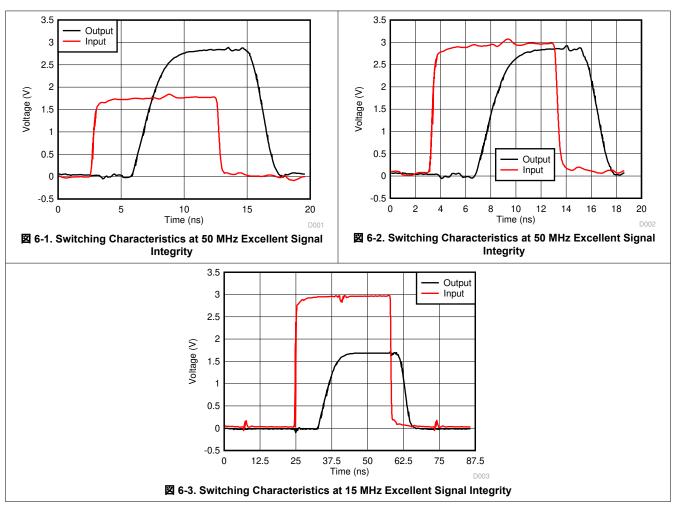
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# **6.8 Typical Characteristics**

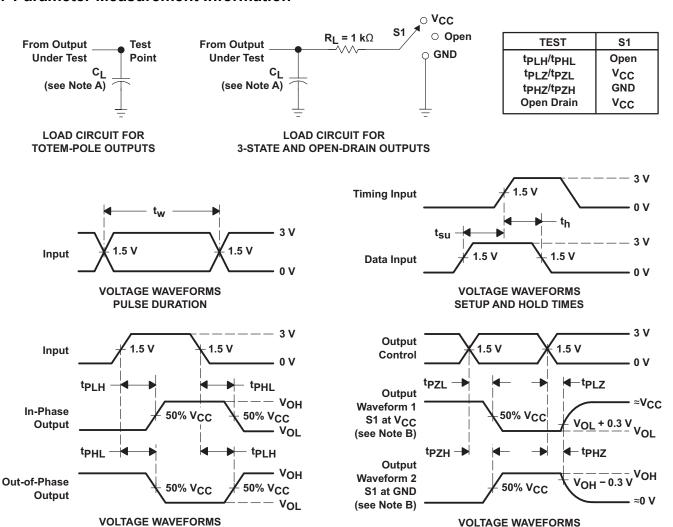


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## 7 Parameter Measurement Information



NOTES: A.  $C_L$  includes probe and jig capacitance.

PROPAGATION DELAY TIMES

INVERTING AND NONINVERTING OUTPUTS

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O$  = 50  $\Omega$ ,  $t_f \leq$  3 ns.
- D. The outputs are measured one at a time, with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

図 7-1. Load Circuit and Voltage Waveforms

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**ENABLE AND DISABLE TIMES** 

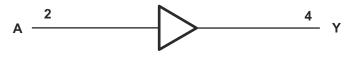
**LOW- AND HIGH-LEVEL ENABLING** 

## 8 Detailed Description

#### 8.1 Overview

The SN74LV1T34 device is a low-voltage CMOS gate logic that operates at a wider voltage range for industrial, portable, telecom, and automotive applications. The output level is referenced to the supply voltage and is able to support 1.8-V, 2.5-V, 3.3-V, and 5-V CMOS levels. The input is designed with a lower threshold circuit to match 1.8 V input logic at  $V_{CC}$  = 3.3 V and can be used in 1.8 V to 3.3 V level-up translation. In addition, the 5 V tolerant input pins enable down translation (that is, 3.3 V to 2.5 V output at  $V_{CC}$  = 2.5 V). The wide  $V_{CC}$  range of 1.8 V to 5.5 V allows generation of desired output levels to connect to controllers or processors. The SN74LV1T34 device is designed with current-drive capability of 8 mA to reduce line reflections, overshoot, and undershoot caused by high-drive outputs.

## 8.2 Functional Block Diagram



# 図 8-1. Logic Diagram

#### 8.3 Feature Description

## 8.3.1 Clamp Diode Structure

The outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only as depicted in  $\boxtimes$  8-2.

#### 注意

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

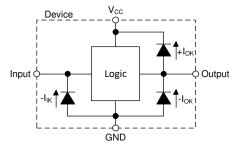


図 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

# 8.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Product Folder Links: SN74LV1T34

Unused push-pull CMOS outputs should be left disconnected.

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#### 8.3.3 LVxT Enhanced Input Voltage

The SN74LV1T34 belongs to TI's LVxT family of Logic devices with integrated voltage level translation. This family of devices was designed with reduced input voltage thresholds to support up-translation, and inputs tolerant of signals with up to 5.5 V levels to support down-translation. The output voltage will always be referenced to the supply voltage ( $V_{CC}$ ), as described in the *Electrical Characteristics* table. To ensure proper functionality, input signals must remain at or below the specified  $V_{IH(MIN)}$  level for a HIGH input state, and at or below the specified  $V_{IL(MAX)}$  for a LOW input state.  $\boxtimes$  8-3 shows the typical  $V_{IH}$  and  $V_{IL}$  levels for the LVxT family of devices, as well as the voltage levels for standard CMOS devices for comparison.

The inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law  $(R = V \div I)$ .

The inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the *Implications of Slow or Floating CMOS Inputs* application report.

Do not leave inputs floating at any time during operation. Unused inputs must be terminated at  $V_{CC}$  or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a  $10-k\Omega$  resistor is recommended and will typically meet all requirements.

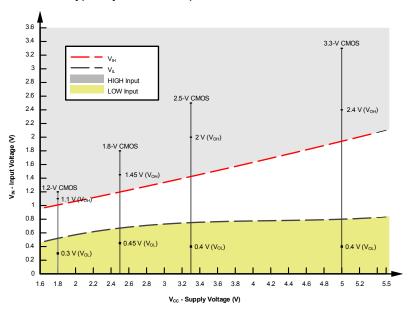


図 8-3. LVxT Input Voltage Levels

#### 8.3.3.1 Down Translation

Signals can be translated down using the SN74LV1T34. The voltage applied at the  $V_{CC}$  will determine the output voltage and the input thresholds as described in the *Recommended Operating Conditions* and *Electrical Characteristics* tables.

When connected to a high-impedance input, the output voltage will be approximately  $V_{CC}$  in the HIGH state, and 0 V in the LOW state. Ensure that the input signals in the HIGH state are between  $V_{IH(MIN)}$  and 5.5 V, and input signals in the LOW state are lower than  $V_{IL(MAX)}$  as shown in  $\boxtimes$  8-3.

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For example, standard CMOS inputs for devices operating at 5.0 V, 3.3 V or 2.5 V can be down-translated to match 1.8 V CMOS signals when operating from 1.8-V  $V_{CC}$ . See  $\boxtimes$  8-4.

#### **Down Translation Combinations:**

- 1.8-V V<sub>CC</sub> Inputs from 2.5 V, 3.3 V, and 5.0 V
- 2.5-V V<sub>CC</sub> Inputs from 3.3 V and 5.0 V
- 3.3-V V<sub>CC</sub> Inputs from 5.0 V

## 8.3.3.2 Up Translation

Input signals can be up translated using the SN74LV1T34. The voltage applied at  $V_{CC}$  will determine the output voltage and the input thresholds as described in the *Recommended Operating Conditions* and *Electrical Characteristics* tables. When connected to a high-impedance input, the output voltage will be approximately  $V_{CC}$  in the HIGH state, and 0 V in the LOW state.

The inputs have reduced thresholds that allow for input high-state levels which are much lower than standard values. For example, standard CMOS inputs for a device operating at a 5-V supply will have a  $V_{IH(MIN)}$  of 3.5 V. For the SN74LV1T34,  $V_{IH(MIN)}$  with a 5-V supply is only 2 V, which would allow for up-translation from a typical 2.5-V to 5-V signals.

Ensure that the input signals in the HIGH state are above  $V_{IH(MIN)}$  and input signals in the LOW state are lower than  $V_{IL(MAX)}$  as shown in  $\boxtimes$  8-4.

#### Up Translation Combinations:

- 1.8-V V<sub>CC</sub> Inputs from 1.2 V
- 2.5-V V<sub>CC</sub> Inputs from 1.8 V
- 3.3-V V<sub>CC</sub> Inputs from 1.8 V and 2.5 V
- 5.0-V V<sub>CC</sub> Inputs from 2.5 V and 3.3 V

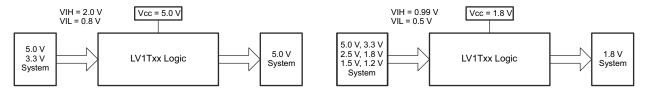


図 8-4. LVxT Up and Down Translation Example

#### 8.4 Device Functional Modes

表 8-1 is the function table for the SN74LV1T34.

表 8-1. Function Table

INPUT (LOWER LEVEL INPUT)	OUTPUT (V <sub>CC</sub> CMOS)
Α	Y
Н	Н
L	L

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## 9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

# 9.1 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in the following layout example.

#### 9.2 Layout

#### 9.2.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V<sub>CC</sub>, whichever makes more sense for the logic function or is more convenient.

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# 10 Device and Documentation Support

## 10.1 Documentation Support (Analog)

#### 10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, CMOS Power Consumption and Cpd Calculation application note
- Texas Instruments, *Designing With Logic* application note
- Texas Instruments, Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices application note
- Texas Instruments, Implications of Slow or Floating CMOS Inputs application note

### 10.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

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#### 10.6 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

#### 11 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision D (November 2023) to Revision E (February 2024)	Page	
Updated RθJA values: DBV = 206 to 278, all values in °C/W	7	
Changes from Revision C (June 2017) to Revision D (November 2023)	Page	
Changes from Revision C (June 2017) to Revision D (November 2023)  「パッケージ情報」表にパッケージ サイズを追加	<u>-</u>	

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# 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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English Data Sheet: SCLS743

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Product Folder Links: SN74LV1T34

www.ti.com 23-May-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
	(-)	(-)			(5)	(4)	(5)		(-)
SN74LV1T34DBVR	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(3B3H, 3CJF, NEJ3, NEJJ, NEJS)
SN74LV1T34DBVR.A	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(3B3H, 3CJF, NEJ3, NEJJ, NEJS)
SN74LV1T34DBVRG4	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	NEJ3
SN74LV1T34DBVRG4.A	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	NEJ3
SN74LV1T34DCKR	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(1R4, WJ3, WJJ, WJ S)
SN74LV1T34DCKR.A	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(1R4, WJ3, WJJ, WJ S)
SN74LV1T34DCKRG4	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-	WJ3
SN74LV1T34DCKRG4.A	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	WJ3

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE OPTION ADDENDUM**

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#### OTHER QUALIFIED VERSIONS OF SN74LV1T34:

Automotive: SN74LV1T34-Q1

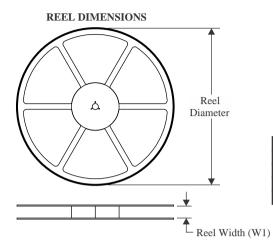
NOTE: Qualified Version Definitions:

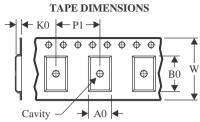
Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

**PACKAGE MATERIALS INFORMATION** 

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

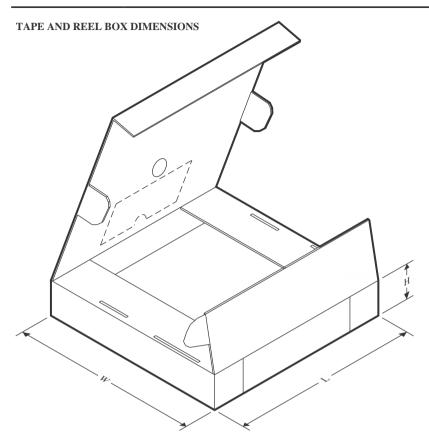


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV1T34DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LV1T34DBVRG4	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LV1T34DCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74LV1T34DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3



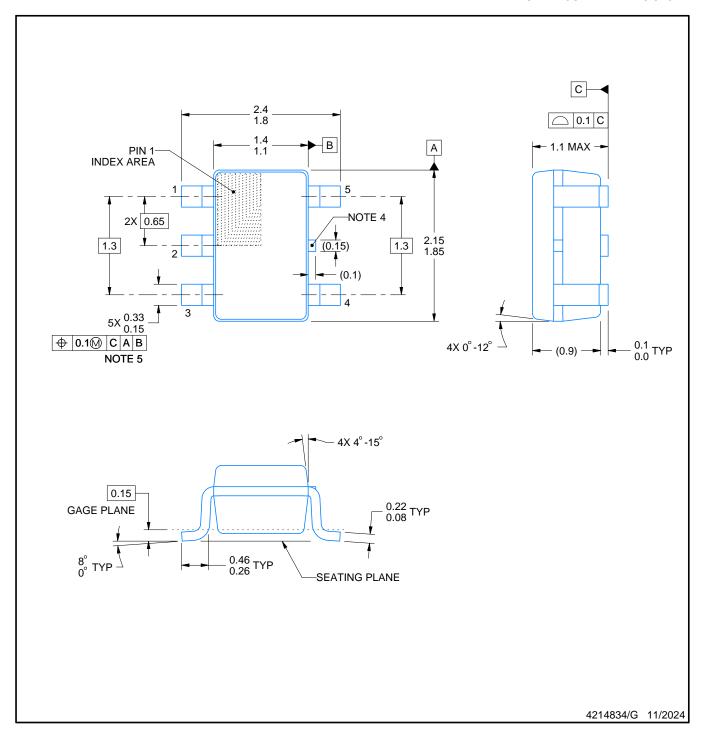
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#### \*All dimensions are nominal

7 til dilliololololo di o liolililai							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV1T34DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74LV1T34DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LV1T34DCKR	SC70	DCK	5	3000	210.0	185.0	35.0
SN74LV1T34DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0



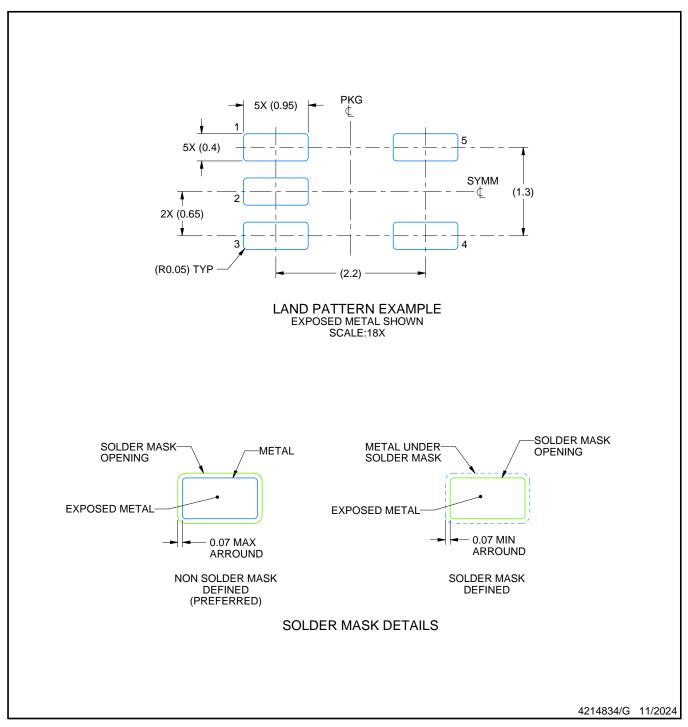


#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

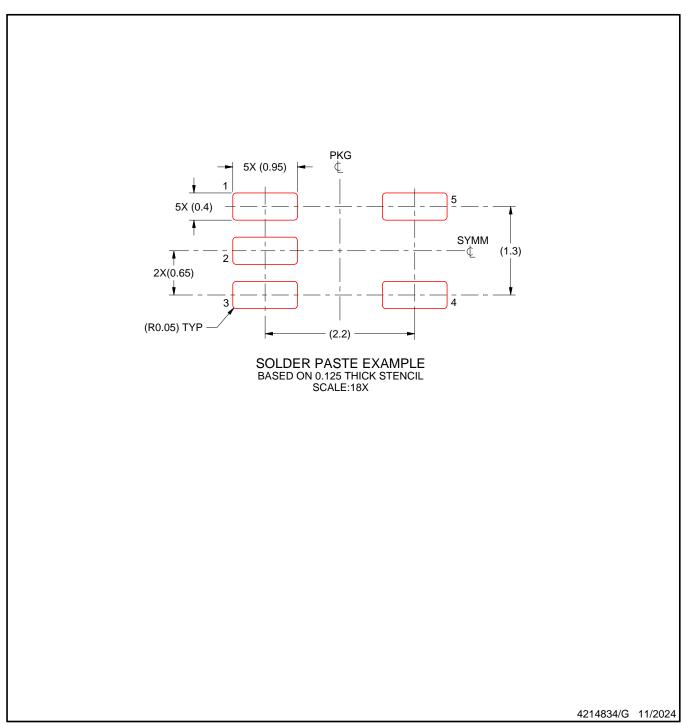




NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.







#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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